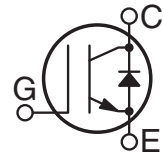
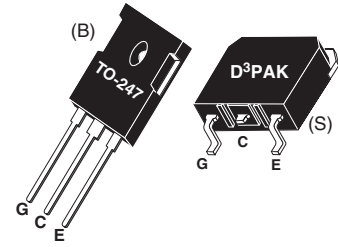


Utilizing the latest Field Stop and Trench Gate technologies, these IGBT's have ultra low $V_{CE(ON)}$ and are ideal for low frequency applications that require absolute minimum conduction loss. Easy paralleling is a result of very tight parameter distribution and a slightly positive $V_{CE(ON)}$ temperature coefficient. Low gate charge simplifies gate drive design and minimizes losses.

- 1200V Field Stop
- Trench Gate: Low $V_{CE(on)}$
- Easy Paralleling



Applications: Welding, Inductive Heating, Solar Inverters, SMPS, Motor drives, UPS

MAXIMUM RATINGS

All Ratings: $T_C = 25^\circ\text{C}$ unless otherwise specified.

Symbol	Parameter	APT15GN120BD_SDQ1(G)	UNIT
V_{CES}	Collector-Emitter Voltage	1200	Volts
V_{GE}	Gate-Emitter Voltage	± 30	
I_{C1}	Continuous Collector Current @ $T_C = 25^\circ\text{C}$	45	Amps
I_{C2}	Continuous Collector Current @ $T_C = 110^\circ\text{C}$	22	
I_{CM}	Pulsed Collector Current ^①	45	
SSOA	Switching Safe Operating Area @ $T_J = 150^\circ\text{C}$	45A @ 1200V	
P_D	Total Power Dissipation	195	Watts
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to 150	$^\circ\text{C}$
T_L	Max. Lead Temp. for Soldering: 0.063" from Case for 10 Sec.	300	

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	Units
$V_{(BR)CES}$	Collector-Emitter Breakdown Voltage ($V_{GE} = 0V, I_C = 0.5mA$)	1200			Volts
$V_{GE(TH)}$	Gate Threshold Voltage ($V_{CE} = V_{GE}, I_C = 600\mu A, T_j = 25^\circ\text{C}$)	5.0	5.8	6.5	
$V_{CE(ON)}$	Collector-Emitter On Voltage ($V_{GE} = 15V, I_C = 15A, T_j = 25^\circ\text{C}$)	1.4	1.7	2.1	
	Collector-Emitter On Voltage ($V_{GE} = 15V, I_C = 15A, T_j = 125^\circ\text{C}$)		2.0		
I_{CES}	Collector Cut-off Current ($V_{CE} = 1200V, V_{GE} = 0V, T_j = 25^\circ\text{C}$) ^②			200	μA
	Collector Cut-off Current ($V_{CE} = 1200V, V_{GE} = 0V, T_j = 125^\circ\text{C}$) ^②			TBD	
I_{GES}	Gate-Emitter Leakage Current ($V_{GE} = \pm 20V$)			120	nA
R_{GINT}	Intergrated Gate Resistor		N/A		Ω



CAUTION: These Devices are Sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

DYNAMIC CHARACTERISTICS

APT15GN120BD_SDQ1(G)

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT	
C_{ies}	Input Capacitance	Capacitance $V_{GE} = 0V, V_{CE} = 25V$ $f = 1 \text{ MHz}$		1200		pF	
C_{oes}	Output Capacitance			65			
C_{res}	Reverse Transfer Capacitance			50			
V_{GEP}	Gate-to-Emitter Plateau Voltage	Gate Charge $V_{GE} = 15V$ $V_{CE} = 600V$ $I_C = 15A$		9.0		V	
Q_g	Total Gate Charge ^③			90		nC	
Q_{ge}	Gate-Emitter Charge			5			
Q_{gc}	Gate-Collector ("Miller") Charge			55			
SSOA	Switching Safe Operating Area	$T_J = 150^\circ\text{C}, R_G = 4.3\Omega^{\text{⑦}}, V_{GE} = 15V, L = 100\mu\text{H}, V_{CE} = 1200V$	45			A	
$t_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C) $V_{CC} = 800V$ $V_{GE} = 15V$ $I_C = 15A$ $R_G = 4.3\Omega^{\text{⑦}}$ $T_J = +25^\circ\text{C}$		10		ns	
t_r	Current Rise Time			9			
$t_{d(off)}$	Turn-off Delay Time			150			
t_f	Current Fall Time			110			
E_{on1}	Turn-on Switching Energy ^④				410		μJ
E_{on2}	Turn-on Switching Energy (Diode) ^⑤				730		
E_{off}	Turn-off Switching Energy ^⑥				950		
$t_{d(on)}$	Turn-on Delay Time		Inductive Switching (125°C) $V_{CC} = 800V$ $V_{GE} = 15V$ $I_C = 15A$ $R_G = 4.3\Omega^{\text{⑦}}$ $T_J = +125^\circ\text{C}$		10		ns
t_r	Current Rise Time			9			
$t_{d(off)}$	Turn-off Delay Time			170			
t_f	Current Fall Time			185			
E_{on1}	Turn-on Switching Energy ^④				475		μJ
E_{on2}	Turn-on Switching Energy (Diode) ^⑤				1310		
E_{off}	Turn-off Switching Energy ^⑥				1300		

THERMAL AND MECHANICAL CHARACTERISTICS

Symbol	Characteristic	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction to Case (IGBT)			.64	°C/W
$R_{\theta JC}$	Junction to Case (DIODE)			1.18	
W_T	Package Weight		5.9		gm

① Repetitive Rating: Pulse width limited by maximum junction temperature.

② For Combi devices, I_{ces} includes both IGBT and FRED leakages

③ See MIL-STD-750 Method 3471.

④ E_{on1} is the clamped inductive turn-on energy of the IGBT only, without the effect of a commutating diode reverse recovery current adding to the IGBT turn-on loss. Tested in inductive switching test circuit shown in figure 21, but with a Silicon Carbide diode.

⑤ E_{on2} is the clamped inductive turn-on energy that includes a commutating diode reverse recovery current in the IGBT turn-on switching loss. (See Figures 21, 22.)

⑥ E_{off} is the clamped inductive turn-off energy measured in accordance with JEDEC standard JESD24-1. (See Figures 21, 23.)

⑦ R_G is external gate resistance, not including R_{Gint} nor gate driver impedance. (MIC4452)

Microsemi Reserves the right to change, without notice, the specifications and information contained herein.

TYPICAL PERFORMANCE CURVES

APT15GN120BD_SDQ1(G)

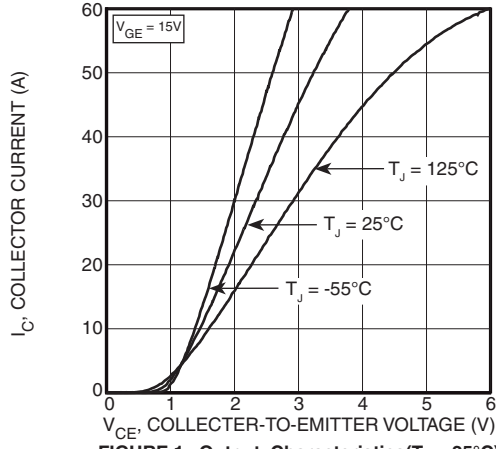


FIGURE 1, Output Characteristics ($T_J = 25^\circ\text{C}$)

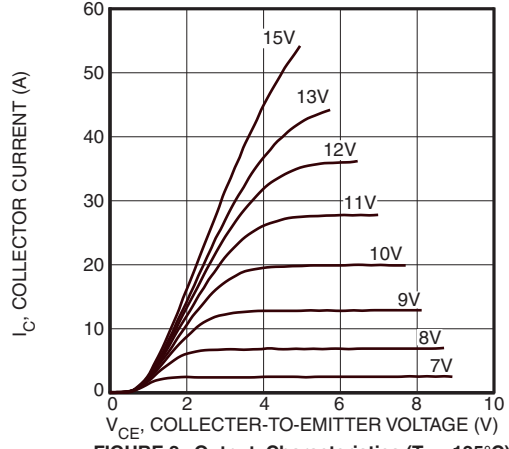


FIGURE 2, Output Characteristics ($T_J = 125^\circ\text{C}$)

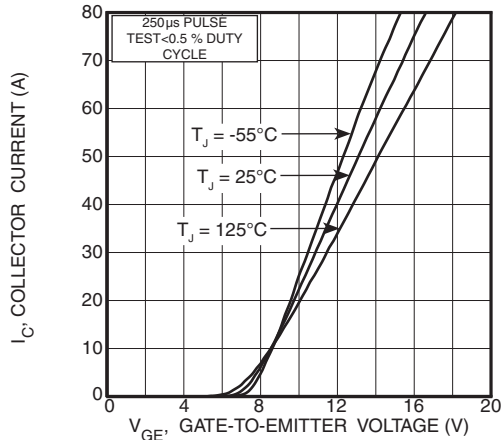


FIGURE 3, Transfer Characteristics

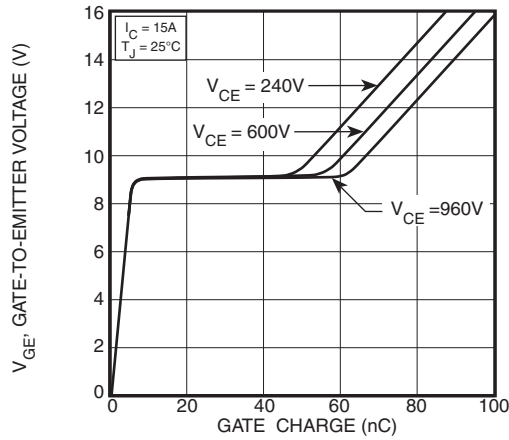


FIGURE 4, Gate Charge

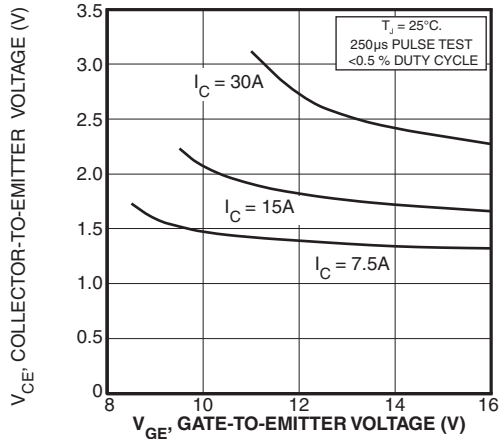


FIGURE 5, On State Voltage vs Gate-to-Emitter Voltage

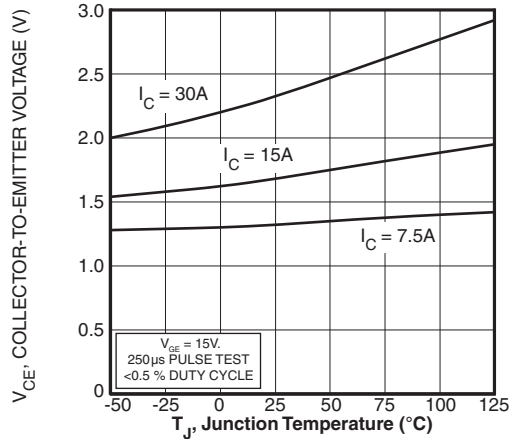


FIGURE 6, On State Voltage vs Junction Temperature

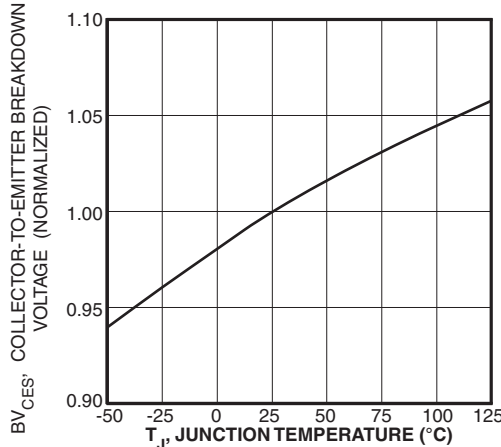


FIGURE 7, Breakdown Voltage vs. Junction Temperature

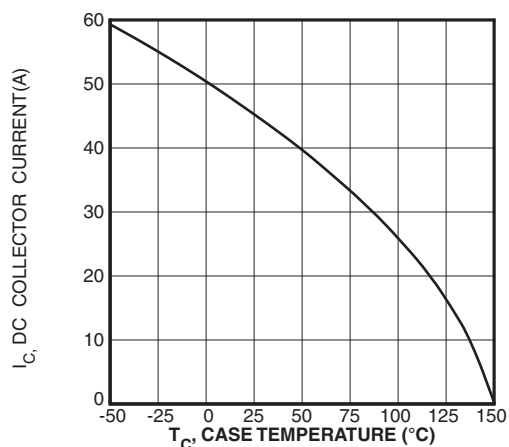


FIGURE 8, DC Collector Current vs Case Temperature

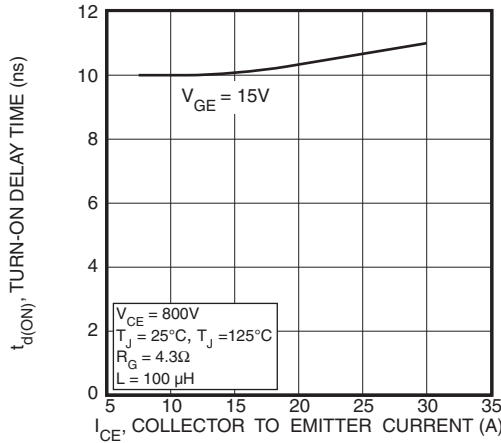


FIGURE 9, Turn-On Delay Time vs Collector Current

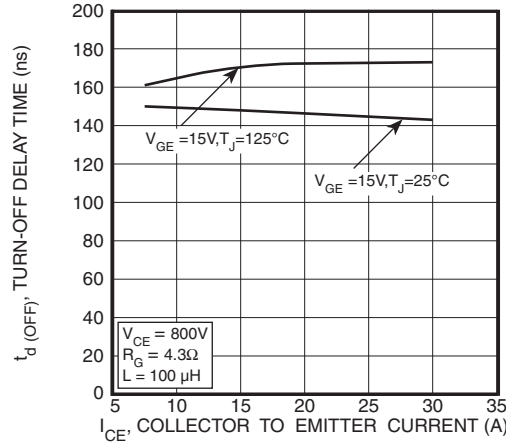


FIGURE 10, Turn-Off Delay Time vs Collector Current

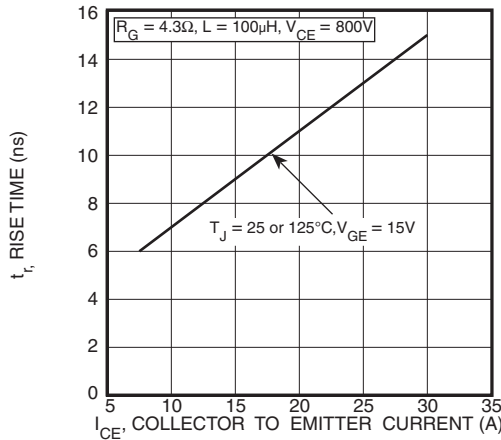


FIGURE 11, Current Rise Time vs Collector Current

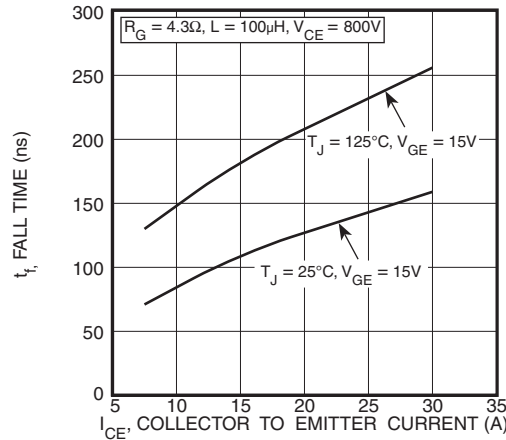


FIGURE 12, Current Fall Time vs Collector Current

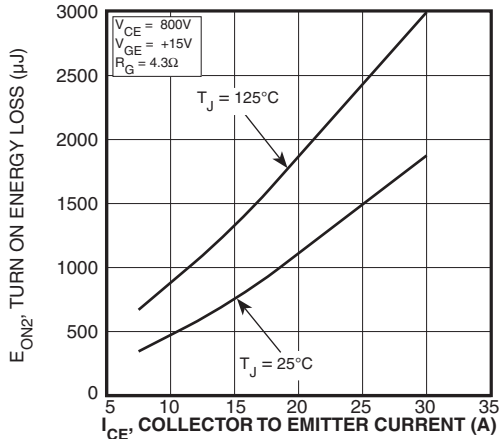


FIGURE 13, Turn-On Energy Loss vs Collector Current

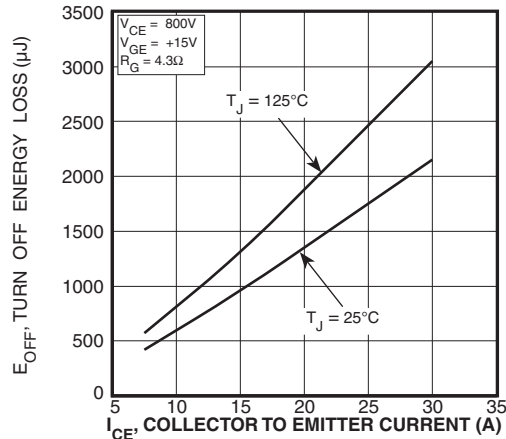


FIGURE 14, Turn Off Energy Loss vs Collector Current

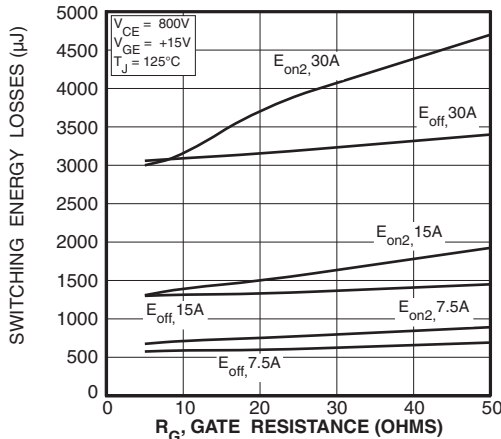


FIGURE 15, Switching Energy Losses vs. Gate Resistance

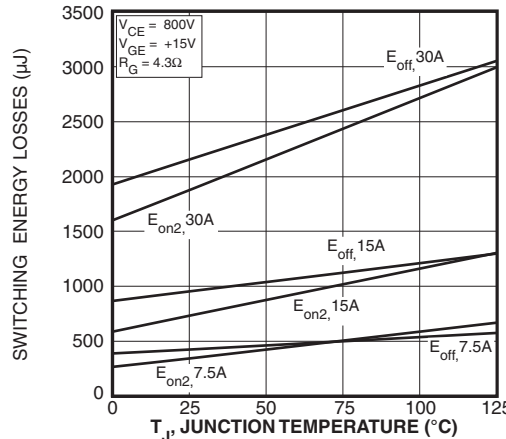


FIGURE 16, Switching Energy Losses vs Junction Temperature

TYPICAL PERFORMANCE CURVES

APT15GN120BD_SDQ1(G)

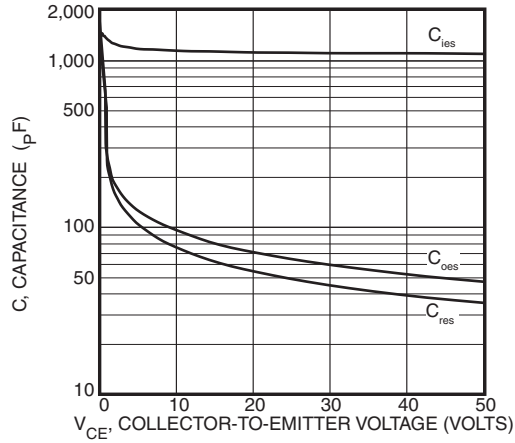


Figure 17, Capacitance vs Collector-To-Emitter Voltage

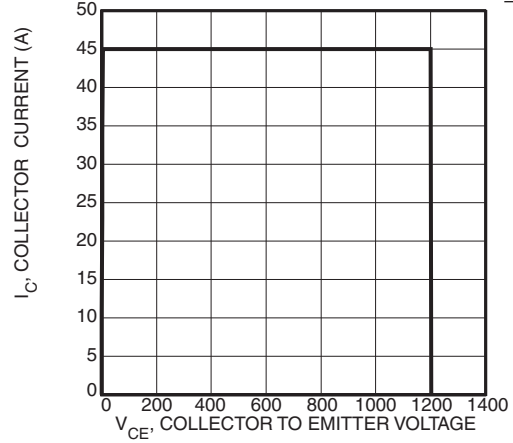


Figure 18, Minimum Switching Safe Operating Area

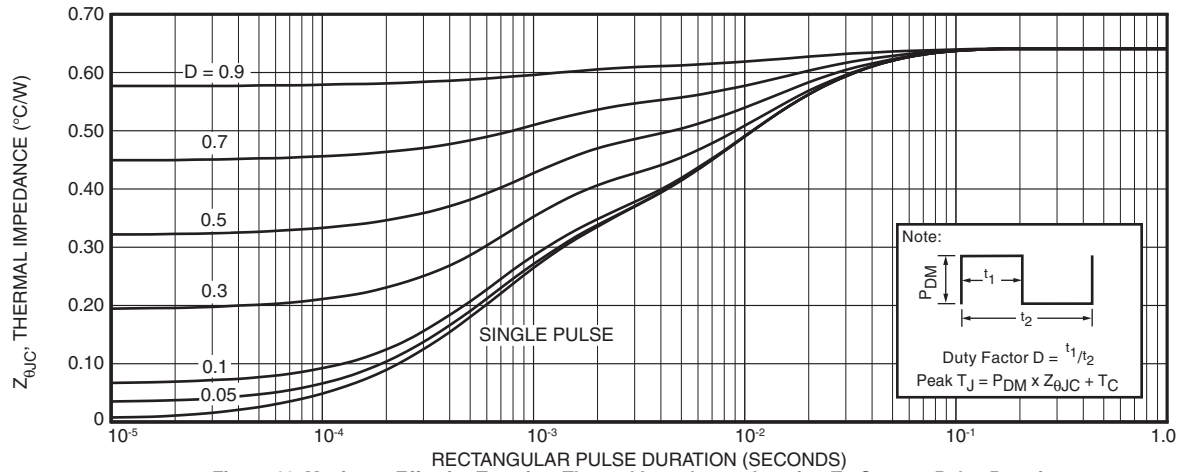


Figure 19, Maximum Effective Transient Thermal Impedance, Junction-To-Case vs Pulse Duration

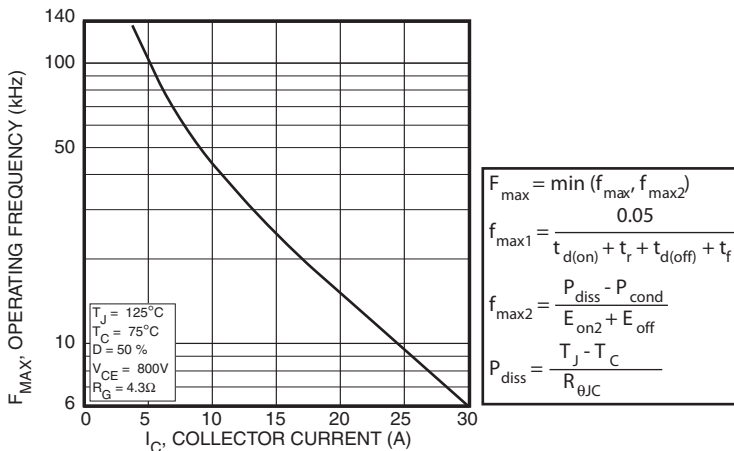


Figure 20, Operating Frequency vs Collector Current

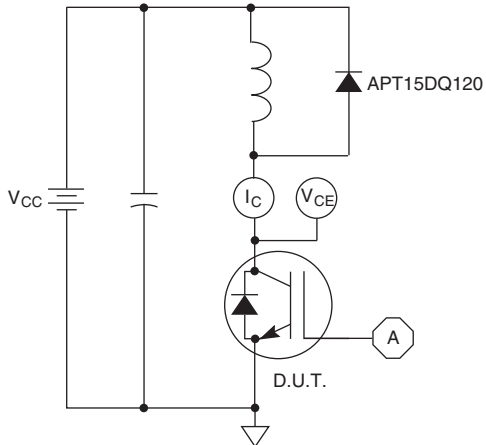


Figure 21, Inductive Switching Test Circuit

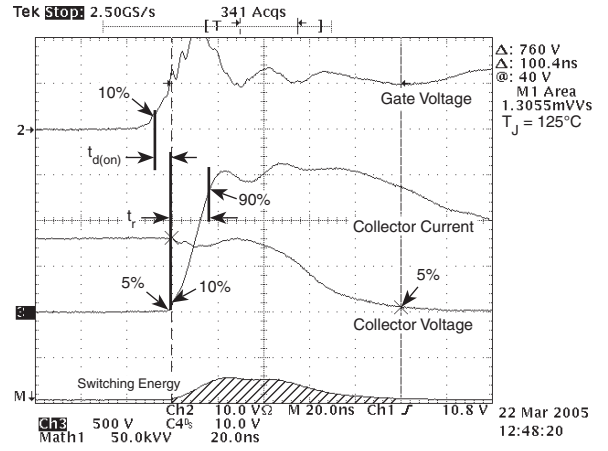


Figure 22, Turn-on Switching Waveforms and Definitions

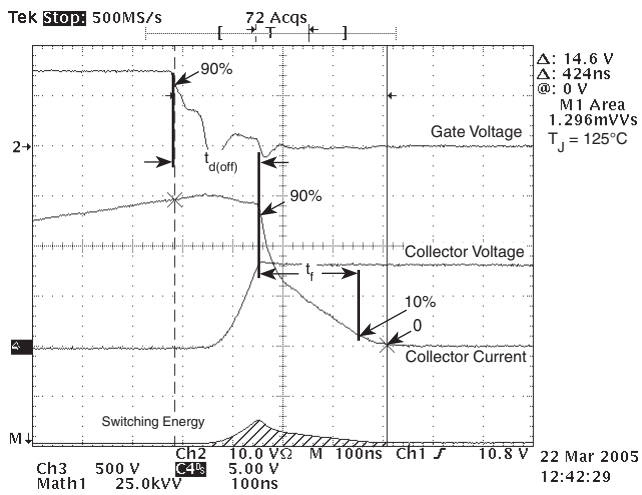


Figure 23, Turn-off Switching Waveforms and Definitions

ULTRAFAST SOFT RECOVERY ANTI-PARALLEL DIODE

MAXIMUM RATINGS

All Ratings: $T_C = 25^\circ\text{C}$ unless otherwise specified.

Symbol	Characteristic / Test Conditions	APT15GN120BD_SDQ1(G)		UNIT
$I_F(AV)$	Maximum Average Forward Current ($T_C = 127^\circ\text{C}$, Duty Cycle = 0.5)		15	Amps
$I_F(RMS)$	RMS Forward Current (Square wave, 50% duty)		29	
I_{FSM}	Non-Repetitive Forward Surge Current ($T_J = 45^\circ\text{C}$, 8.3ms)		110	

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
V_F	Forward Voltage	$I_F = 15\text{A}$		2.8	Volts
		$I_F = 30\text{A}$		2.4	
		$I_F = 15\text{A}, T_J = 125^\circ\text{C}$		2.45	

DYNAMIC CHARACTERISTICS

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
t_{rr}	Reverse Recovery Time	$I_F = 1\text{A}, di_F/dt = -100\text{A}/\mu\text{s}, V_R = 30\text{V}, T_J = 25^\circ\text{C}$	-	21		ns
t_{rr}	Reverse Recovery Time	$I_F = 15\text{A}, di_F/dt = -200\text{A}/\mu\text{s}, V_R = 800\text{V}, T_C = 25^\circ\text{C}$	-	240		
Q_{rr}	Reverse Recovery Charge		-	260		nC
I_{RRM}	Maximum Reverse Recovery Current		-	3	-	Amps
t_{rr}	Reverse Recovery Time	$I_F = 15\text{A}, di_F/dt = -200\text{A}/\mu\text{s}, V_R = 800\text{V}, T_C = 125^\circ\text{C}$	-	290		ns
Q_{rr}	Reverse Recovery Charge		-	960		nC
I_{RRM}	Maximum Reverse Recovery Current		-	6	-	Amps
t_{rr}	Reverse Recovery Time	$I_F = 15\text{A}, di_F/dt = -1000\text{A}/\mu\text{s}, V_R = 800\text{V}, T_C = 125^\circ\text{C}$	-	130		ns
Q_{rr}	Reverse Recovery Charge		-	1340		nC
I_{RRM}	Maximum Reverse Recovery Current		-	19		Amps

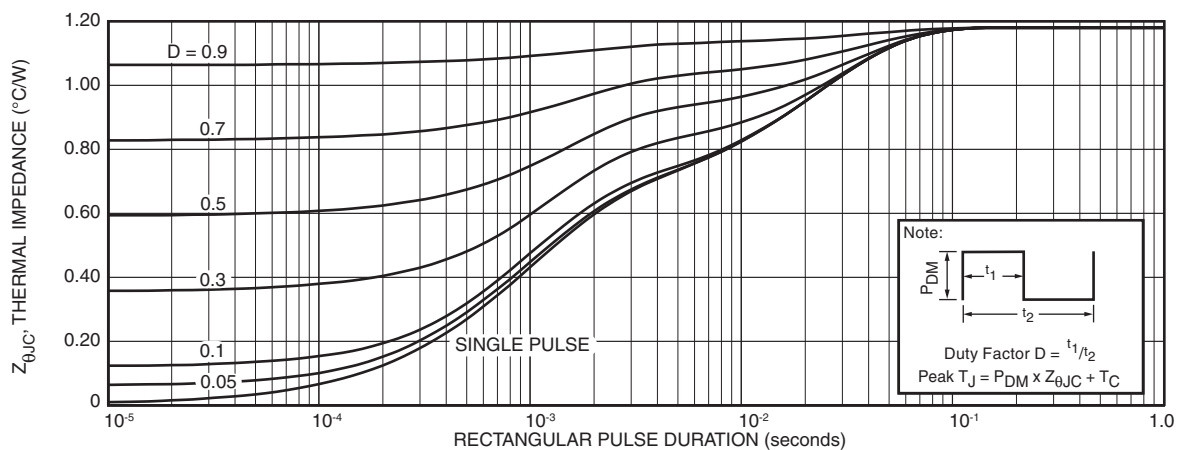


FIGURE 24. MAXIMUM EFFECTIVE TRANSIENT THERMAL IMPEDANCE, JUNCTION-TO-CASE vs. PULSE DURATION

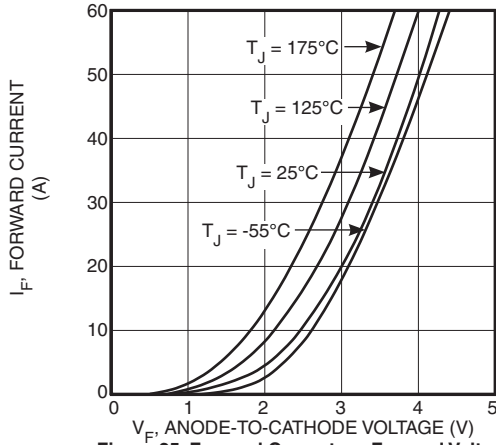


Figure 25. Forward Current vs. Forward Voltage

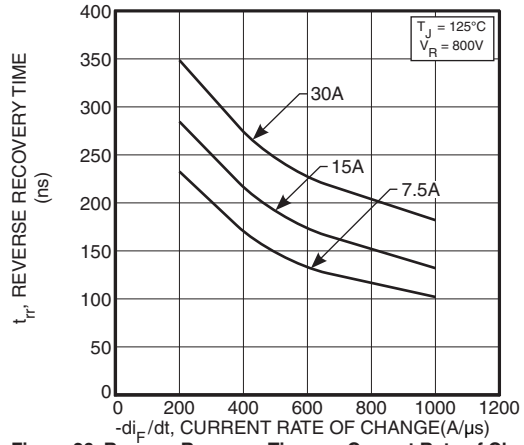


Figure 26. Reverse Recovery Time vs. Current Rate of Change

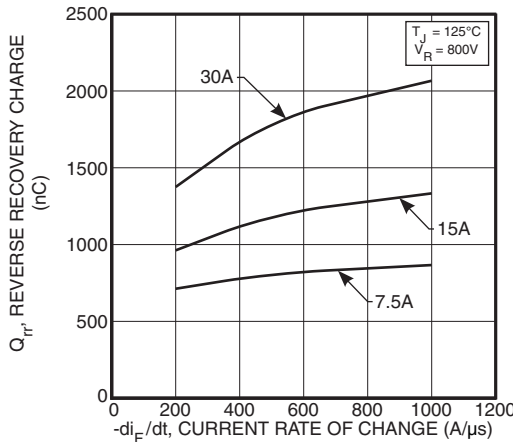


Figure 27. Reverse Recovery Charge vs. Current Rate of Change

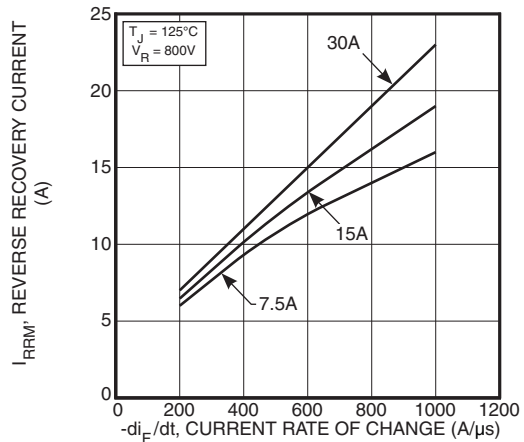


Figure 28. Reverse Recovery Current vs. Current Rate of Change

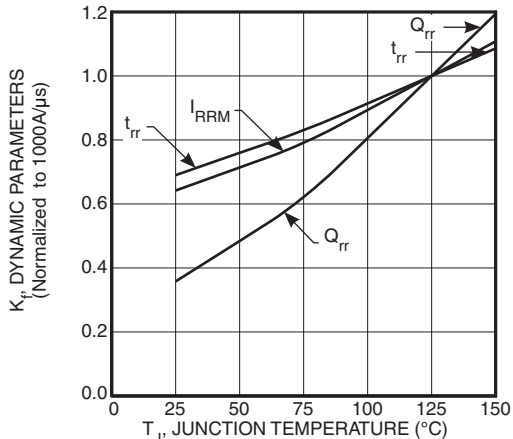


Figure 29. Dynamic Parameters vs. Junction Temperature

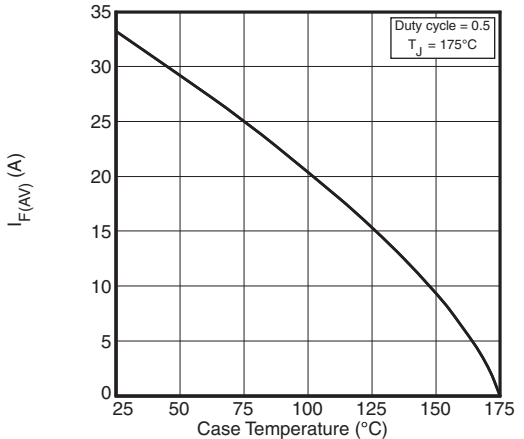


Figure 30. Maximum Average Forward Current vs. Case Temperature

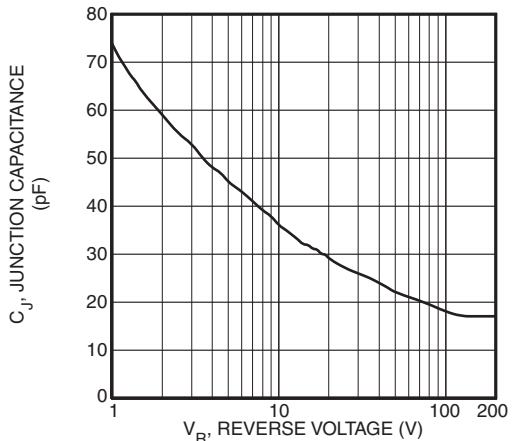


Figure 31. Junction Capacitance vs. Reverse Voltage

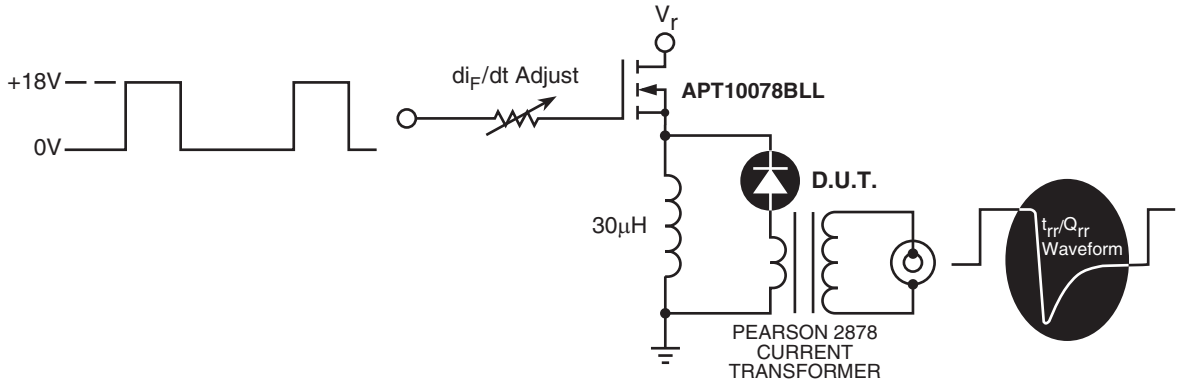


Figure 32. Diode Test Circuit

- 1 I_F - Forward Conduction Current
- 2 di_F/dt - Rate of Diode Current Change Through Zero Crossing.
- 3 I_{RRM} - Maximum Reverse Recovery Current.
- 4 t_{rr} - Reverse Recovery Time, measured from zero crossing where diode current goes from positive to negative, to the point at which the straight line through I_{RRM} and $0.25 \cdot I_{RRM}$ passes through zero.
- 5 Q_{rr} - Area Under the Curve Defined by I_{RRM} and t_{rr} .

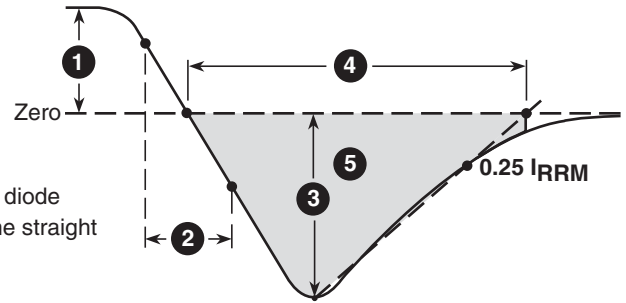
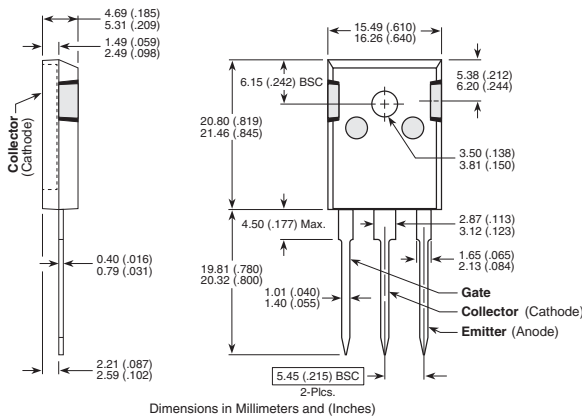


Figure 33, Diode Reverse Recovery Waveform and Definitions

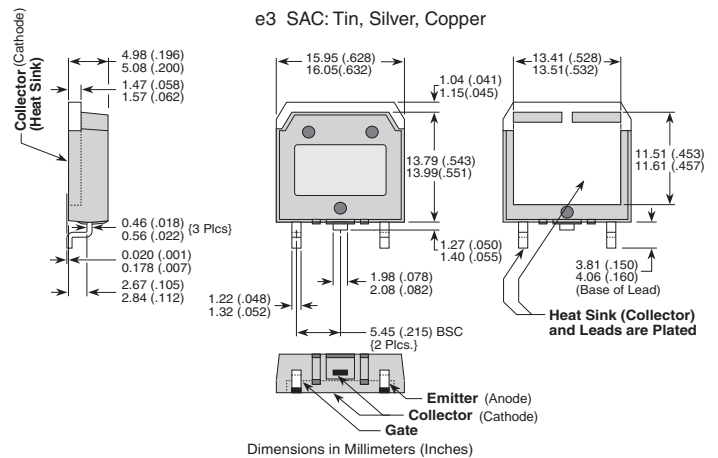
TO-247 Package Outline

e1 SAC: Tin, Silver, Copper



D³PAK Package Outline

e3 SAC: Tin, Silver, Copper



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Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

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